

85V N-Channel Trench MOSFET(Preliminary)

General Description		Product Summ	ary
Trench Power Technology		VDS	85V
• Low R _{DS(ON)}			4054
 Low Gate Charge 		I _D (at V _{GS} =10V)	105A
• Optimized for fast-switching	Applications	R _{DS(ON)} (at V _{GS} =10V)	< 8.5mΩ
 Applications Synchronous Rectification i Isolated DC/DC Converters 		100% UIS Tested	RoHS
TO-263 G D S	TO-220	s	Drain Gate
Device	Package	Form	Marking
TTB105N08A	TO-263	Tape & Reel	105N08A
TTP105N08A	TO-220	Tube	105N08A

Absolute Maximum Ratings (T _A =25°C unless otherwise noted)						
Parameter Drain-Source Voltage		Symbol	Maximum	Units		
		V _{DS}	85	V		
Gate-Source Voltage		V _{GS}	±20	V		
Continuous Drain Current ^B	T _C = 25°C		105			
	$T_{\rm C} = 100^{\rm o}{\rm C}$	ID	73	A		
Pulsed Drain Current ^A	•	I _{DM}	315	A		
Avalanche Current ^A		I _{AS}	47	А		
Single Pulse Avalanche Energy L	=0.3mH ^A	E _{AS}	331	mJ		
Power Dissipation ^C	T _C = 25°C		195	W		
	$T_{\rm C} = 100^{\rm o}{\rm C}$		97	W		
Operating Junction and Storage Temperature Range		T _J , T _{SGT}	-55 to 175	℃		

Thermal Resistance Parameter Symbol Maximum Units Thermal Resistance, Junction-to-Case Steady-State R_{thJC} 0.77 °C/W Thermal Resistance, Junction-to-Ambient Steady-State R_{thJA} 100 °C/W

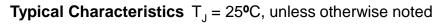


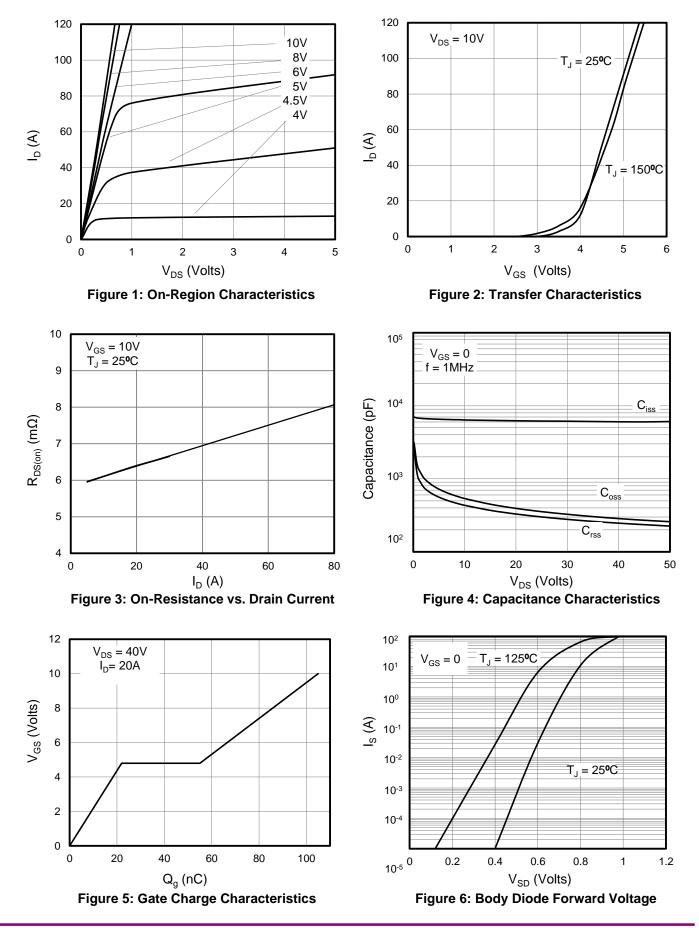
Electric	cal Characteristics(T _J =25°C ur	nless otherwise r	noted)				
0	Demonster	Conditions		Value			
Symbol	Parameter			Min	Тур	Max	Units
STATIC P	ARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	$I_{\rm D} = 250 \mu {\rm A}, V_{\rm GS} = 0 {\rm V}$		85			V
			T _J =25⁰C			1	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{\rm DS} = 85 \text{V}, V_{\rm GS} = 0 \text{V}$	T _J =100°C			25	μA
I _{GSS}	Gate-Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-			±100	nA
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2	3	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 30A$			7.1	8.5	mΩ
g _{fs}	Forward Transconductance	$V_{\rm DS} = 5V, I_{\rm D} = 20A$		80			S
V _{SD}	Diode Forward Voltage	I _S = 20A, V _{GS} = 0V				1	V
I _s	Maximum Body-Diode Continuous Current				105	А	
DYNAMIC	PARAMETERS						
C _{iss}	Input Capacitance				6033		
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 40V, f = 1MH_Z$			285		pF
C _{rss}	Reverse Transfer Capacitance				247		
SWITCHI	NG PARAMETERS	·			-		
Q _g (10V)	Total Gate Charge				105		
Q _{gs}	Gate Source Charge	V _{GS} =10V,V _{DS} = 40V, I _D = 20A			33		nC
Q_{gd}	Gate Drain Charge				22		
t _{D(on)}	Turn-On Delay Time				24		
t _r	Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 40V, I_{D} = 20A, R_{G} = 2.5\Omega$			19		ns
T _{D(off)}	Turn-Off Delay Time				70		
t _f	Turn-Off Fall Time				30		
t _{rr}	Body Diode Reverse Recovery Time				37		ns
Q _{rr}	Body Diode Reverse Recovery Charge	—I _F =20A, di/dt =100A/μs			58		nC

A. Single pulse width limited by maximum junction temperature.

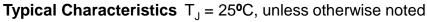
- B. The maximum current rating is package limited.
- C. The power dissipation P_D is based on $T_{J(MAX)} = 175^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.











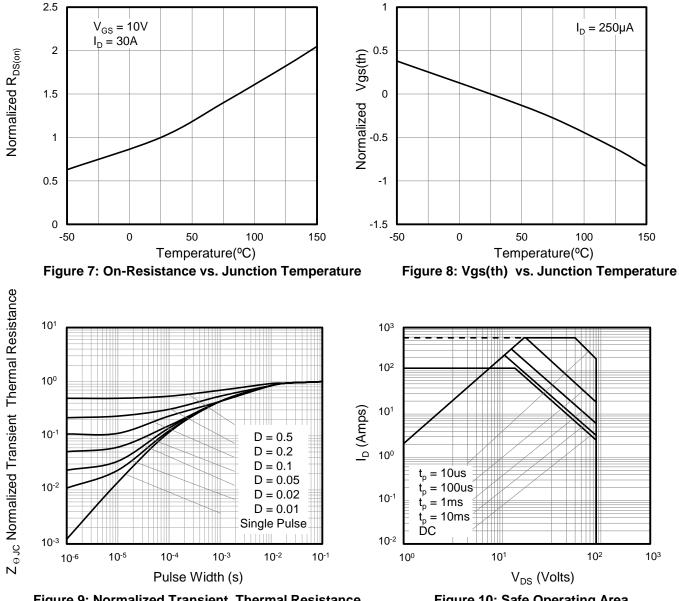




Figure 10: Safe Operating Area



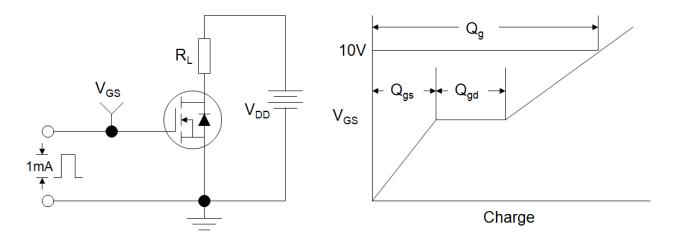


Figure B: Resistive Switching Test Circuit and Waveform

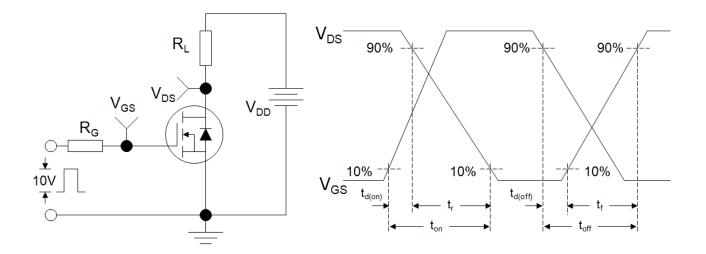
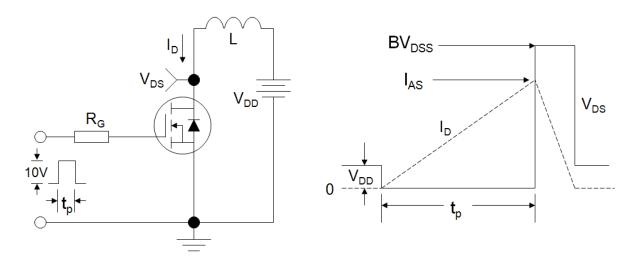
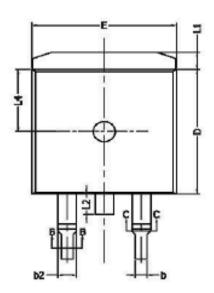


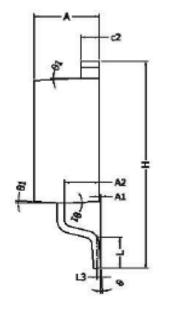
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

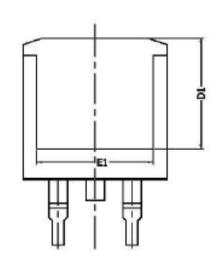




TO-263(集佳)

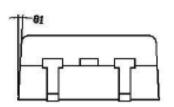






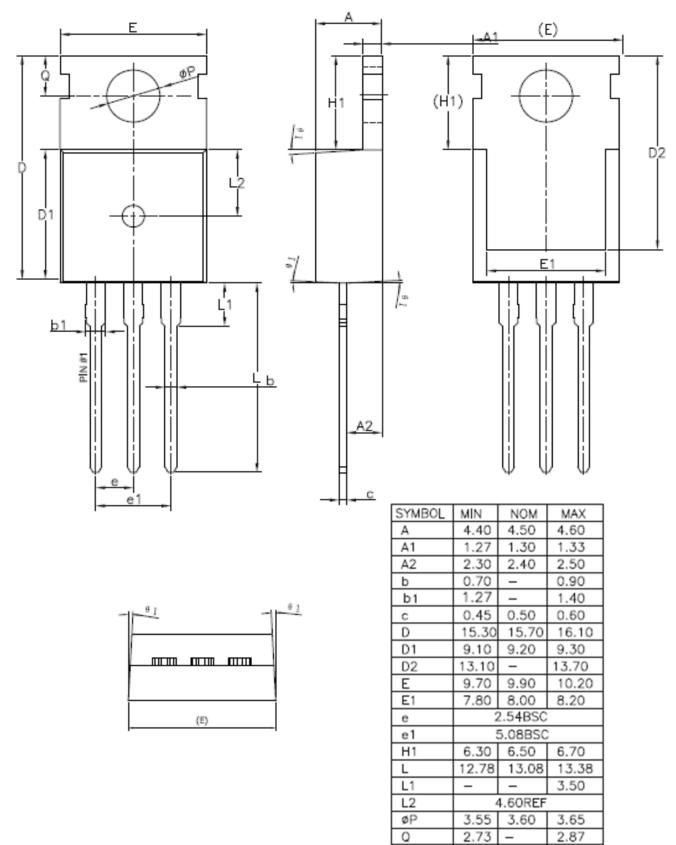
COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
A	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2.20	2.40	2.60	
b	0.76		0.89	
b1	0.75	0.80	0.85	
b2	1.23		1.37	
b3	1.22	1.27	1.32	
C	0.47	-	0.60	
c1	0.46	0.51	0.56	
c2	1.25	1.30	1.35	
D	9.10	9.20	9.30	
D1	8.00		(<u> </u>	
E	9.80	9.90	10.00	
E1	7.80			
e	2.54 BSC			
н	14.90	15.30	15.70	
L	2.00	2.30	2.60	
L1	1.17	1.27	1.40	
12			1.75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°		8°	
01	1°	3°	5°	





TO-220(集佳)



θ1

1*

3

5'



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